

NTHL080N120SC1

MOSFET – Power, N-Channel, Silicon Carbide, TO-247-3L

1200 V, 80 mΩ

Description

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

Features

- 1200 V @ $T_J = 175^{\circ}\text{C}$
- Max $R_{DS(on)} = 110\text{ m}\Omega$ at $V_{GS} = 20\text{ V}$, $I_D = 20\text{ A}$
- High Speed Switching with Low Capacitance
- 100% UIL Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

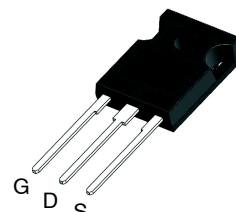
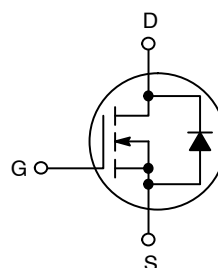
- Industrial Motor Drive
- UPS
- Boost Inverter
- PV Charger



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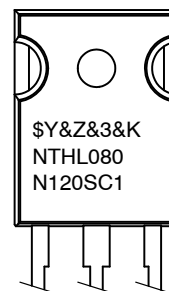
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V_{DS}	$R_{DS(on)}$ TYP	I_D MAX
1200 V	80 mΩ	44 A



TO-247
long leads
CASE 340CX

MARKING DIAGRAM



$\$Y$ = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Data Code (Year & Week)
&K = Lot
NTHL080N120SC1 = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NTHL080N120SC1

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V _{DSmax}	Drain-to-Source Voltage		1200	V
V _{GSmax}	Max. Gate-to-Source Voltage	@ T _C < 150°C	-15 / +25	V
V _{GSop} (DC)	Recommended operation Values of Gate – Source Voltage	@ T _C < 150°C	-5 / +20	V
V _{GSop} (AC)	Recommended operation Values of Gate – Source Voltage (f > 1 Hz)	@ T _C < 150°C	-5 / +20	V
I _D	Continuous Drain Current	V _{GS} = 20 V, T _C = 25°C	44	A
		V _{GS} = 20 V, T _C = 100°C	31	
I _D (Pulse)	Pulse Drain Current	Pulse width tp limited by T _j max	136	A
E _{AS}	Single Pulse Avalanche Energy (Note 1)		171	mJ
P _{tot}	Power Dissipation	T _C = 25°C	348	W
		T _C = 150°C	58	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 171 mJ is based on starting T_J = 25°C, L = 1 mH, I_{AS} = 18.5 A, V_{DD} = 50 V, R_G = 25 Ω.

THERMAL CHARACTERISTICS

Symbol	Parameter	Ratings	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	0.43	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	40	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NTHL080N120SC1	NTHL080N120SC1	TO-247 Long Lead	Tube	N/A	N/A	30 Units

NTHL080N120SC1

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain-to-Source Breakdown Voltage	$I_D = 100\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	1200	–	–	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 5\ \text{mA}$, Referenced to 25°C	–	0.3	–	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1200\ \text{V}$, $V_{GS} = 0\ \text{V}$ $T_C = 25^\circ\text{C}$ $T_C = 150^\circ\text{C}$	– –	– –	100 1.0	μA mA
I_{GSS}	Gate-to-Source Leakage Current	$V_{GS} = 25\ \text{V}$, $V_{DS} = 0\ \text{V}$	–	–	1	μA
I_{GSSR}	Gate-to-Source Leakage Current, Reverse	$V_{GS} = -15\ \text{V}$, $V_{DS} = 0\ \text{V}$	–	–	-1	μA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate-to-Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 5\ \text{mA}$	1.8	2.5	4.3	V
$R_{DS(on)}$	Static Drain-to-Source On Resistance	$V_{GS} = 20\ \text{V}$, $I_D = 20\ \text{A}$	–	80	110	m Ω
		$V_{GS} = 20\ \text{V}$, $I_D = 20\ \text{A}$, $T_C = 150^\circ\text{C}$	–	114	162	
g_{FS}	Forward Transconductance	$V_{DS} = 20\ \text{V}$, $I_D = 20\ \text{A}$	–	13	–	S
		$V_{DS} = 20\ \text{V}$, $I_D = 20\ \text{A}$, $T_C = 150^\circ\text{C}$	–	11	–	

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 800\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	–	1112	1670	pF
C_{oss}	Output Capacitance		–	80	120	pF
C_{rss}	Reverse Transfer Capacitance		–	6.5	10	pF
E_{oss}	C_{oss} Stored Energy		–	32	–	μJ

SWITCHING CHARACTERISTICS

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 800\ \text{V}$, $I_C = 20\ \text{A}$, $V_{GS} = -5/20\ \text{V}$, $R_G = 4.7\ \Omega$ Inductive Load, $T_C = 25^\circ\text{C}$	–	6.2	13	ns
t_r	Rise Time		–	5.8	12	ns
$t_{d(off)}$	Turn-Off Delay Time		–	28	45	ns
t_f	Fall Time		–	8	16	ns
E_{on}	Turn-on Switching Loss		–	361	–	μJ
E_{off}	Turn-off Switching Loss		–	37	–	μJ
E_{ts}	Total Switching Loss	$V_{DD} = 600\ \text{V}$, $I_D = 20\ \text{A}$ $V_{GS} = -5/20\ \text{V}$	–	398	–	μJ
Q_g	Total Gate Charge		–	56	–	nC
Q_{gs}	Gate-to-Source Charge		–	11	–	nC
Q_{gd}	Gate-to-Drain Charge	$f = 1\ \text{MHz}$, D-S short	–	12	–	nC
R_G	Gate input resistance		–	1.7	–	Ω

DIODE CHARACTERISTICS

V _{SD}	Source-to-Drain Diode Forward Voltage	V _{GS} = -5 V, I _{SD} = 10 A	T _C = 25°C	–	4.0	–	V
			T _C = 150°C	–	3.4	–	
E _{rec}	Reverse Recovery Energy	I _{SD} = 20 A, V _{GS} = -5 V, V _R = 600 V, dI _{SD} /dt = 1000 A/μs	T _C = 150°C	–	29	–	μJ
t _{rr}	Diode Reverse Recovery Time		T _C = 25°C	–	18	–	ns
			T _C = 150°C	–	31	–	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	–	80	–	nC
			T _C = 150°C	–	212	–	
I _{rrm}	Peak Reverse Recovery Current		T _C = 25°C	–	9	–	A
		T _C = 150°C	–	14	–		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

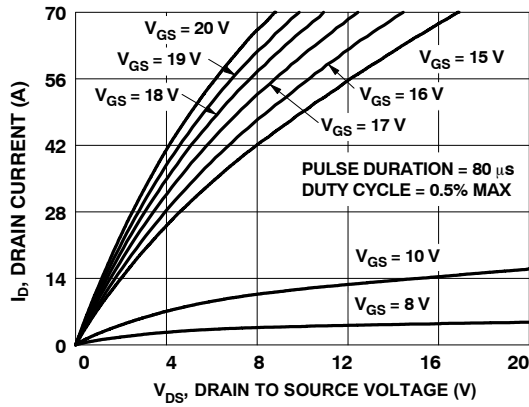


Figure 1. On Region Characteristics

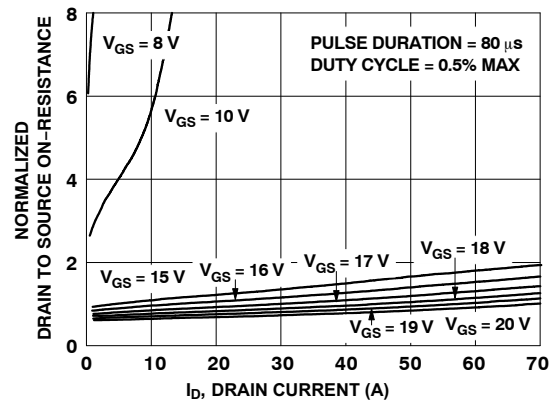


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

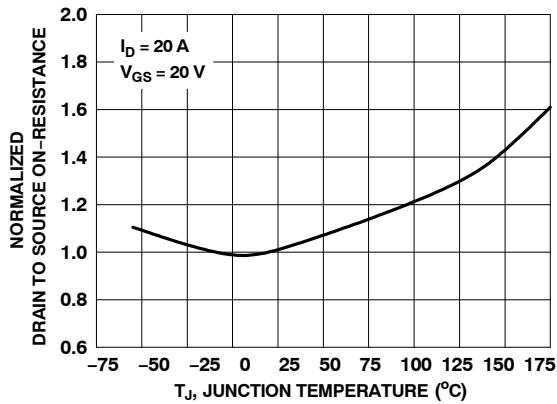


Figure 3. Normalized On Resistance vs. Junction Temperature

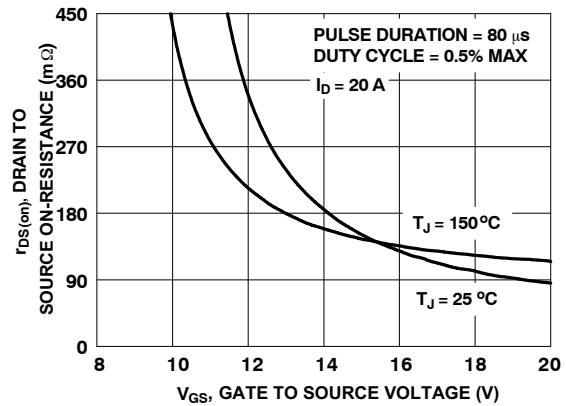


Figure 4. On-Resistance vs. Gate-to-Source Voltage

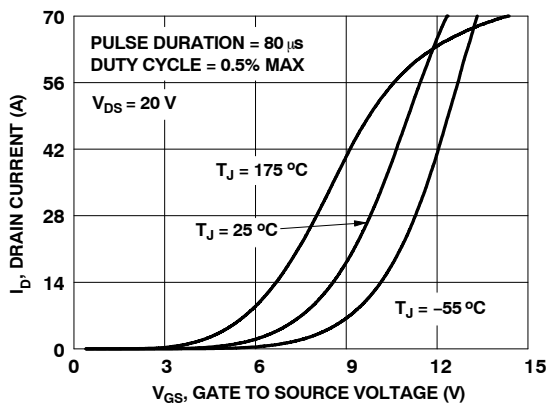


Figure 5. Transfer Characteristics

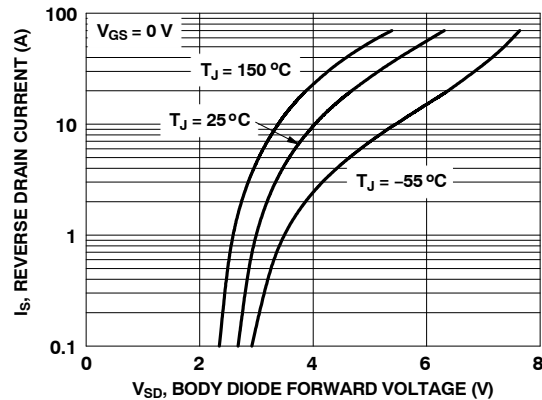


Figure 6. Source-to-Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

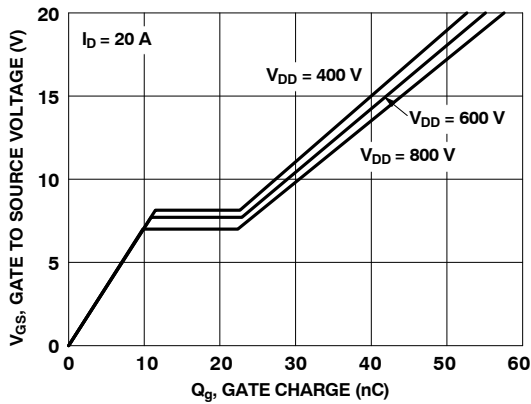


Figure 7. Gate Charge Characteristics

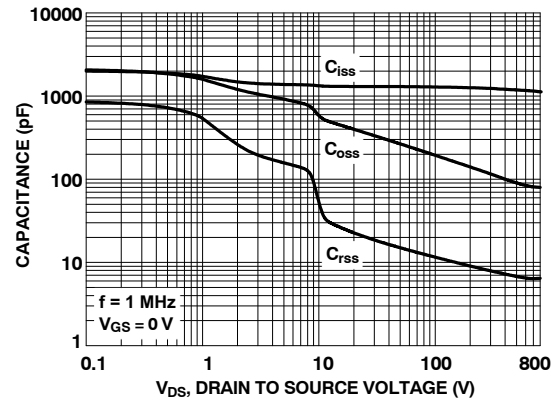


Figure 8. Capacitance vs. Drain-to-Source Voltage

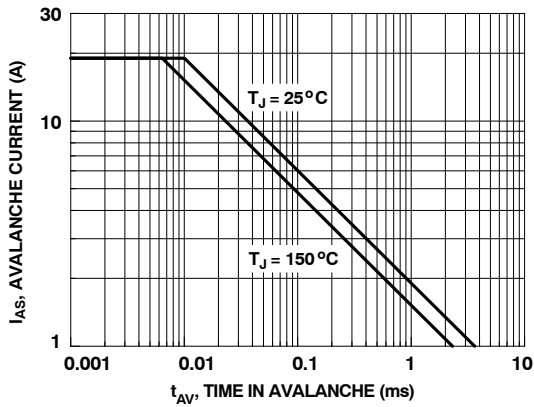


Figure 9. Unclamped Inductive Switching Capability

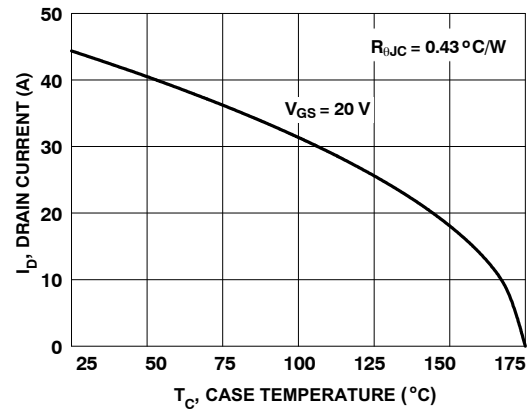


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

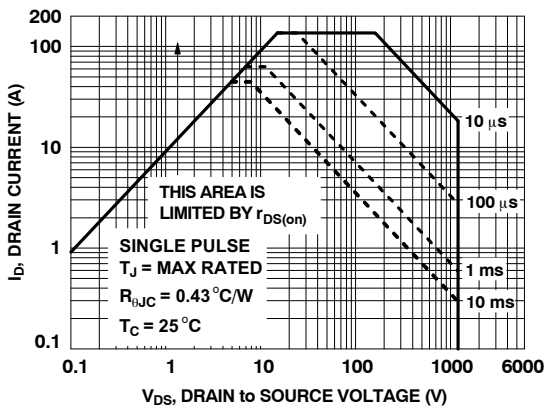


Figure 11. Forward Bias Safe Operating Area

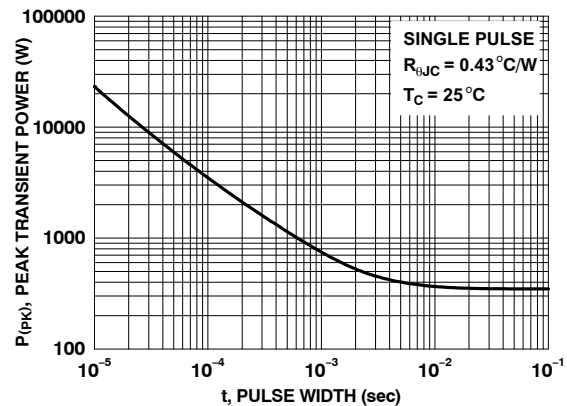


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS $T_J = 25^\circ\text{C}$ unless otherwise noted

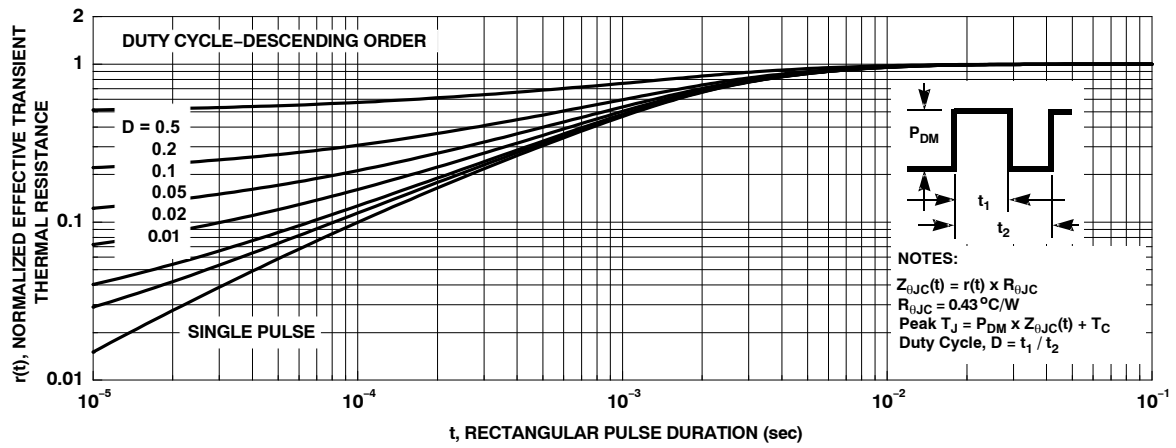
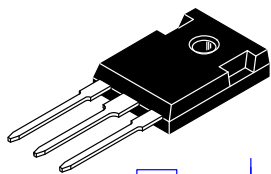


Figure 13. Junction-to-Case Transient Thermal Response Curve

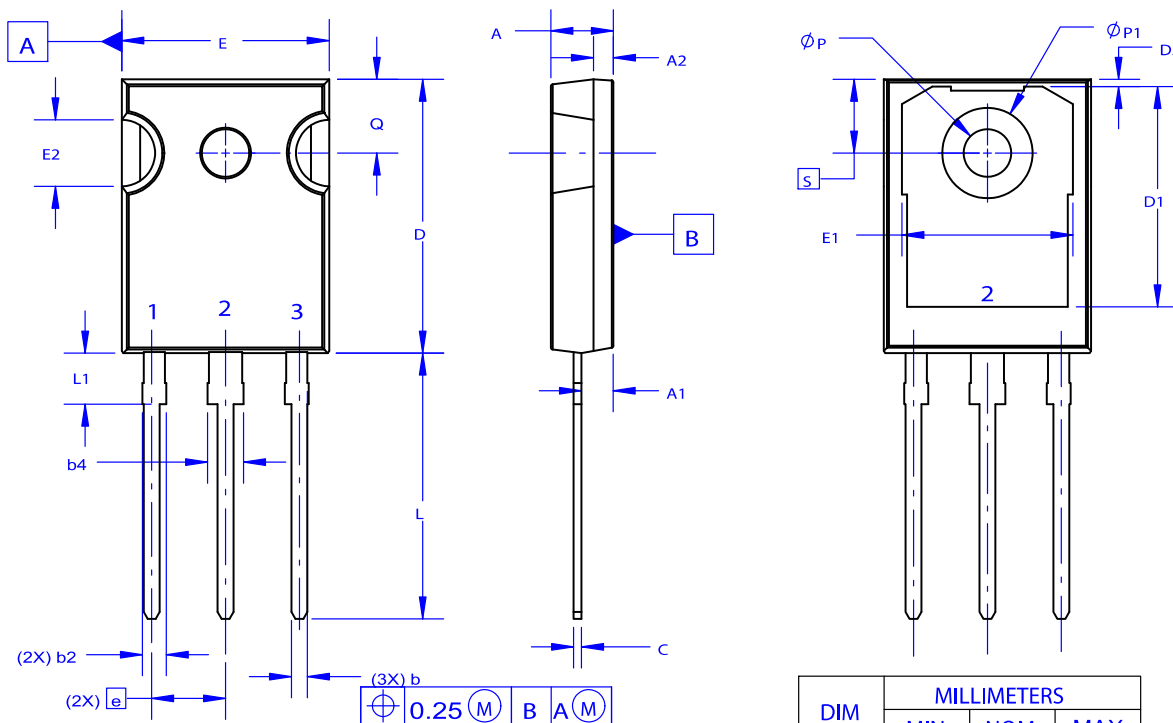
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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TO-247-3LD
CASE 340CX
ISSUE O

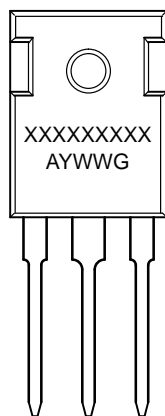
DATE 27 JUN 2018



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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